

ISSP International Summer School for Young Researchers on
“Quantum Transport in Mesoscopic Scale & Low Dimensions”
Aug. 13 - 21, 2003. (My talk is given at 16 Aug. 2003.)

Electrical Conduction in Carbon Nanotubes

T. Nakanishi (AIST)

1. What is Carbon Nanotubes?

Quasi-one dimensional system

2. Effective-Mass Scheme

Electronic properties of carbon nanotubes

3. Impurity Scattering

Ballistic transport

(Absence of back-scattering for Slowly varying potential)

4. Point defects

5. Topological defect

6. Conclusion

Collaborators

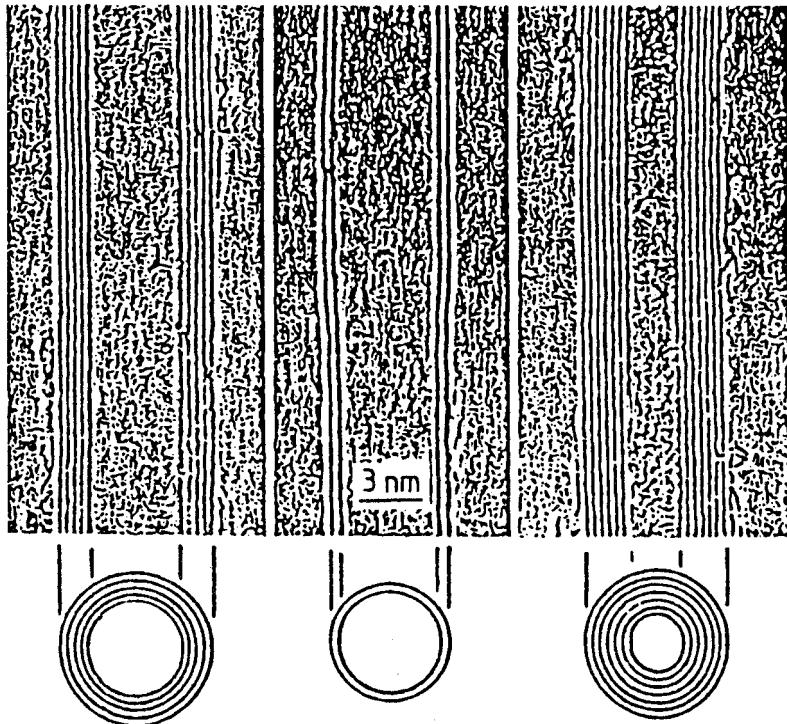
Tsuneya Ando (TIT)

Masatsura Igami (NISTEP)

Riichiro Saito (Tohoku Univ.)

Carbon Nanotubes

Multi-wall

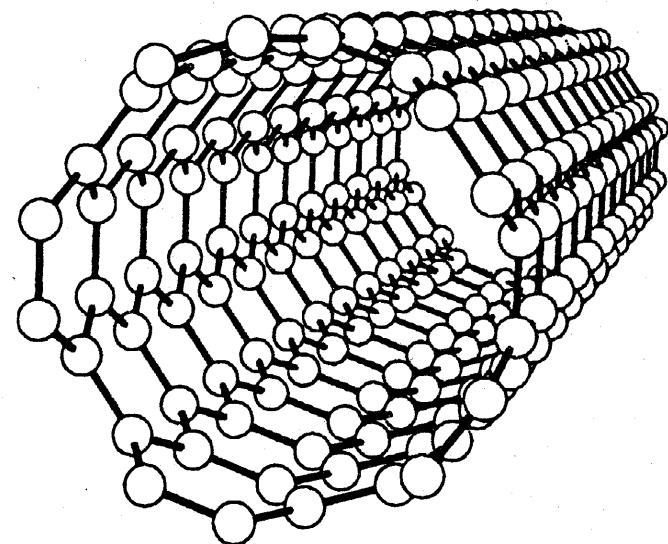


Electron micrographs of CN

S. Iijima, Nature 354, 56 (1991)

Length $\sim 1\mu m$
Diameter $\sim 30\text{nm}$

Single-wall

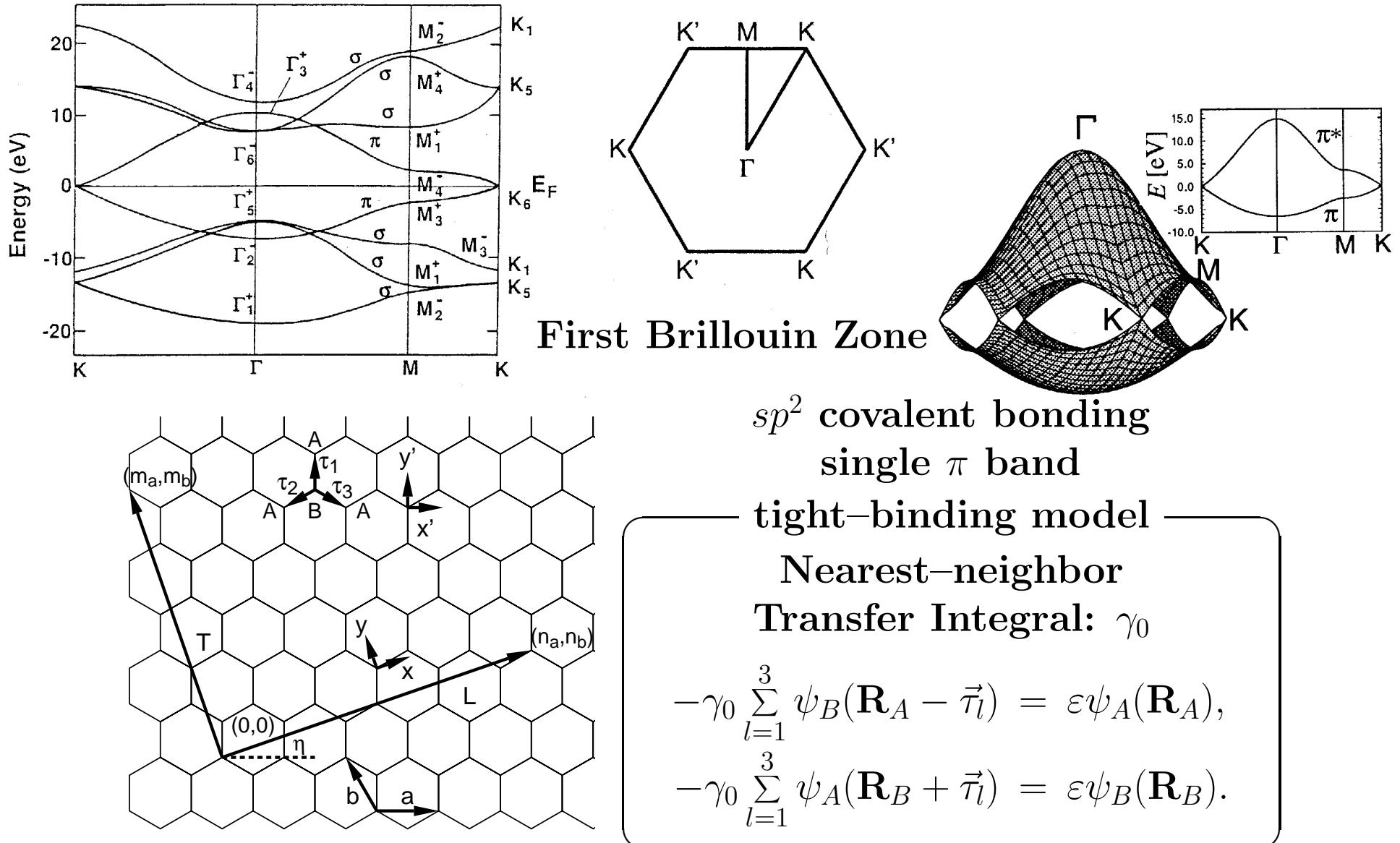


Quantum wire growing naturally

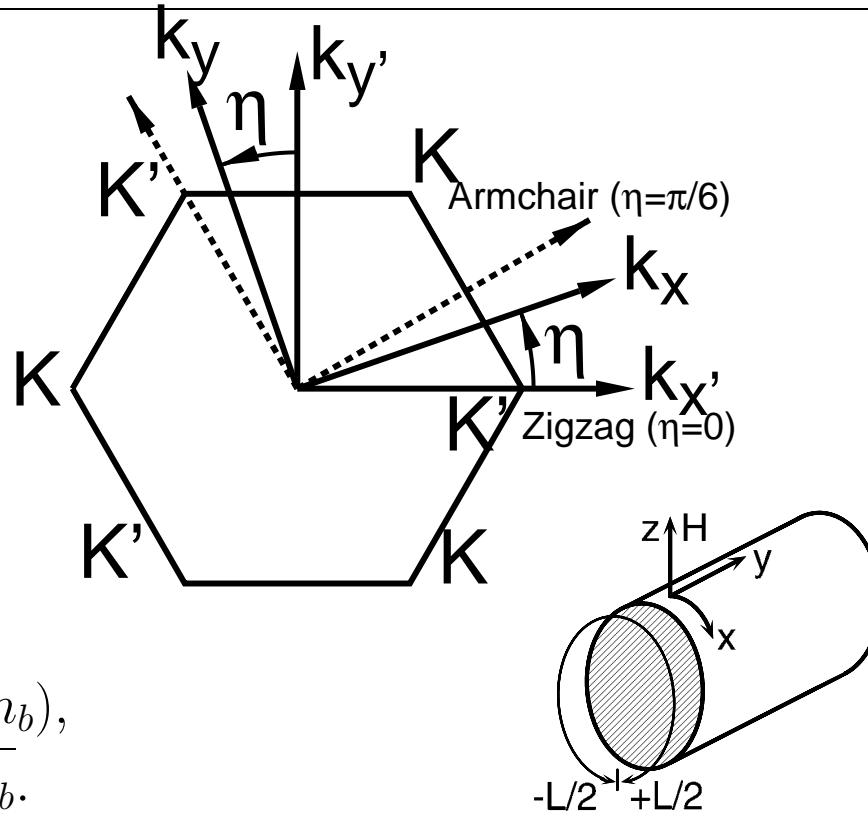
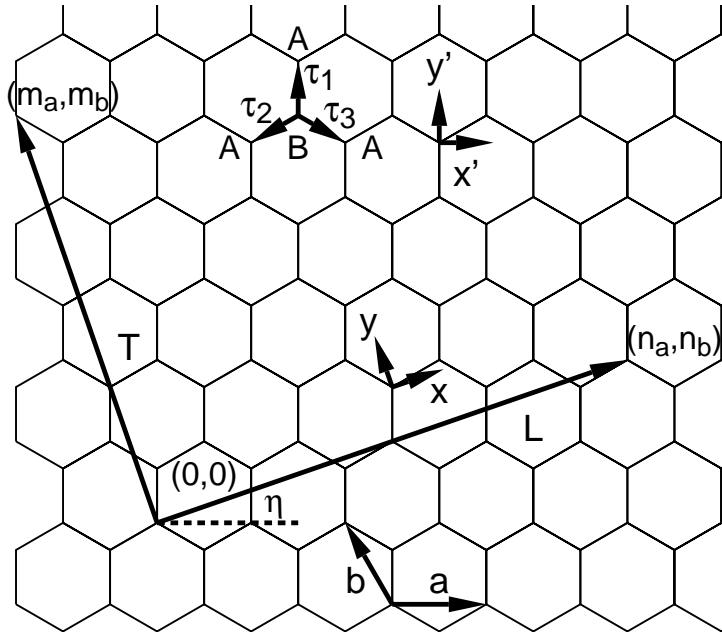
Diameter $\sim 4\text{ nm}$
1D level spacing $\sim 0.8\text{ eV}$

Graphene with periodic
boundary condition

Graphite sheet (Graphene)



Graphite and Chiral Vector



Chiral Vector: $\mathbf{L} = n_a \mathbf{a} + n_b \mathbf{b} \equiv (n_a, n_b),$

$$L = |\mathbf{L}| = a \sqrt{n_a^2 + n_b^2 - n_a n_b}.$$

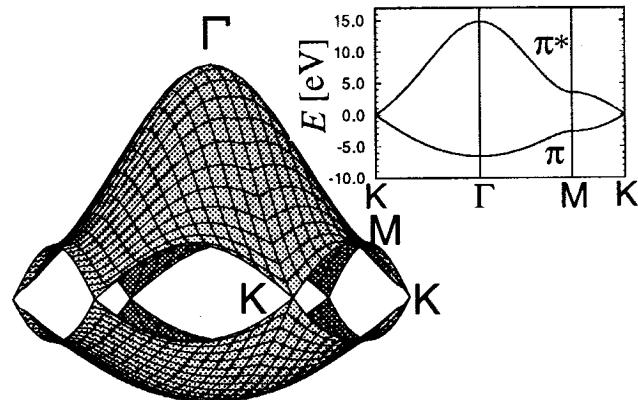
$(n_a, n_b) = (2, 1)m$: **armchair CN**

$(n_a, n_b) = (1, 0)m$: **zigzag CN**

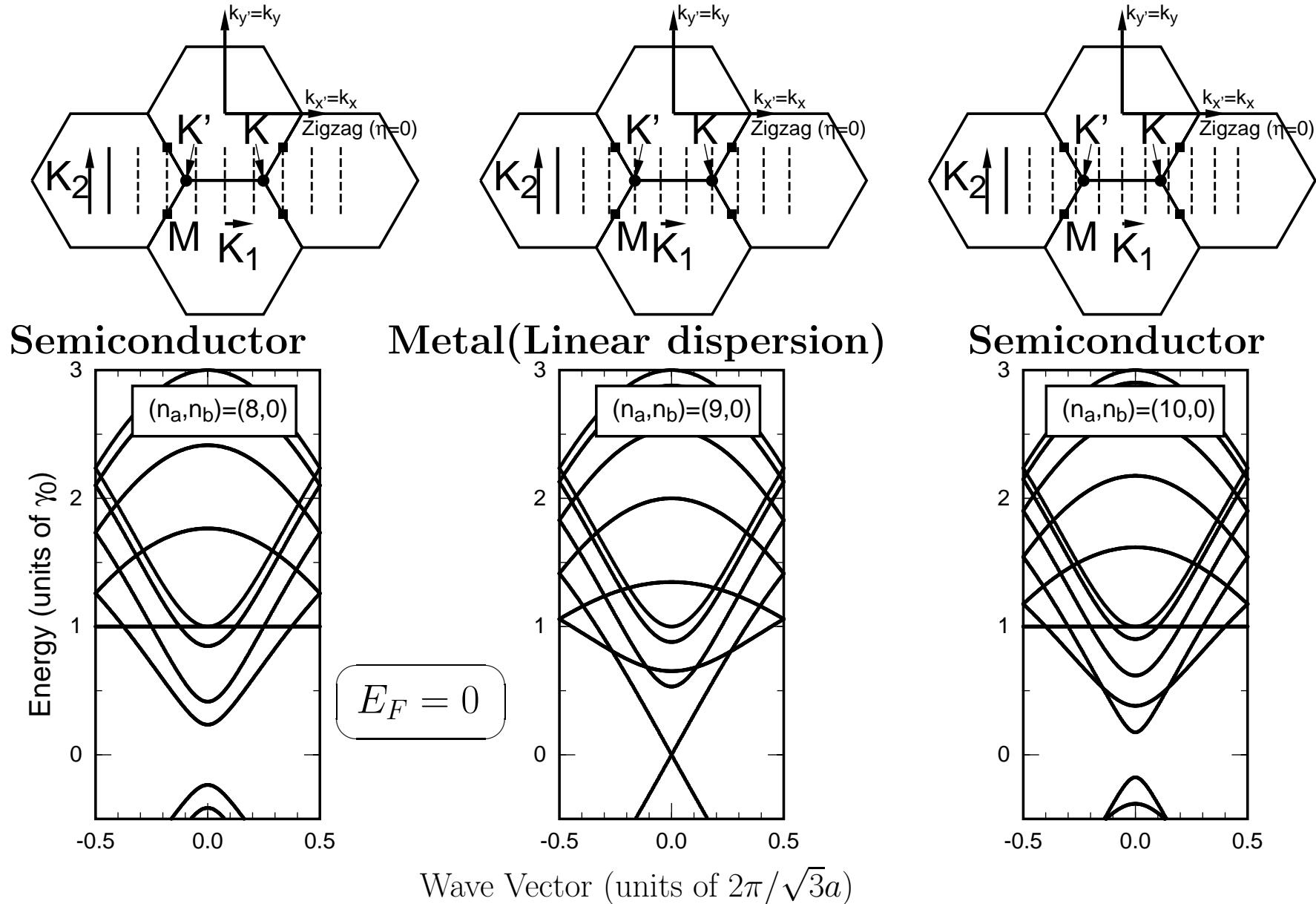
$$n_a + n_b = 3N + \nu$$

$\nu = 0$ **metallic CN**

$\nu = \pm 1$ **semiconducting CN**



Metallic and Semiconducting CN (Zigzag CN)



Effective-mass scheme

$$\mathbf{K} = (2\pi/a)(1/3, 1/\sqrt{3}), \quad \mathbf{K}' = (2\pi/a)(2/3, 0)$$

$$\begin{cases} \psi_A(\mathbf{R}_A) = \exp(i\mathbf{K}\cdot\mathbf{R}_A)F_A^K(\mathbf{R}_A) + e^{i\eta} \exp(i\mathbf{K}'\cdot\mathbf{R}_A)F_A^{K'}(\mathbf{R}_A), \\ \psi_B(\mathbf{R}_B) = -\omega e^{i\eta} \exp(i\mathbf{K}\cdot\mathbf{R}_B)F_B^K(\mathbf{R}_B) + \exp(i\mathbf{K}'\cdot\mathbf{R}_B)F_B^{K'}(\mathbf{R}_B), \end{cases}$$

$F_{A,B}^{K,K'}(\mathbf{R}_{A,B})$: Envelope Functions
 $\omega = \exp(2\pi i/3)$

tight-binding model

$$\begin{aligned} -\gamma_0 \sum_{l=1}^3 \psi_B(\mathbf{R}_A - \vec{\tau}_l) &= \varepsilon \psi_A(\mathbf{R}_A), \\ -\gamma_0 \sum_{l=1}^3 \psi_A(\mathbf{R}_B + \vec{\tau}_l) &= \varepsilon \psi_B(\mathbf{R}_B). \end{aligned}$$

$$\begin{aligned} F_B^{K,K'}(\mathbf{R}_A - \vec{\tau}_l) &= F_B^{K,K'}(\mathbf{R}_A) - \vec{\tau}_l \cdot \frac{\partial}{\partial r_l} F_B^{K,K'}(\mathbf{R}_A) \\ F_A^{K,K'}(\mathbf{R}_B - \vec{\tau}_l) &= F_A^{K,K'}(\mathbf{R}_B) - \vec{\tau}_l \cdot \frac{\partial}{\partial r_l} F_A^{K,K'}(\mathbf{R}_B) \end{aligned}$$

k·p approximation

Effective-Mass Equation

k·p Hamiltonian

K point

$$\begin{pmatrix} 0 & \gamma(\hat{k}_x - i\hat{k}_y) \\ \gamma(\hat{k}_x + i\hat{k}_y) & 0 \end{pmatrix} \begin{pmatrix} F_K^A \\ F_K^B \end{pmatrix} = \varepsilon \begin{pmatrix} F_K^A \\ F_K^B \end{pmatrix}$$

$$\gamma(\sigma_x \hat{k}_x + \sigma_y \hat{k}_y) \mathbf{F}_K(r) = \varepsilon \mathbf{F}_K(r)$$

Weyl's equation for neutrinos

Band Parameter: $\gamma = \sqrt{3}a\gamma_0/2$

Transfer Integral: $\gamma_0 \sim 2.6[\text{eV}]$

$$\hat{\mathbf{k}} = -i\vec{\nabla} + \frac{e}{c\hbar}\mathbf{A}$$

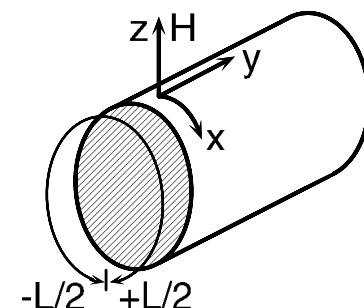
Envelope Function: $\mathbf{F}_K(r)$

$$\mathbf{F}_K(r) = \begin{pmatrix} F_K^A \\ F_K^B \end{pmatrix}$$

K' point

$$\gamma(\sigma_x \hat{k}_x - \sigma_y \hat{k}_y) \mathbf{F}'_K(r) = \varepsilon \mathbf{F}'_K(r)$$

Periodic Boundary Condition in x direction



Electronic States of CN's

Wave functions

$$\mathbf{F}_K(r) = \frac{1}{\sqrt{2}} \begin{pmatrix} b_\nu(n, k_y) \\ \pm 1 \end{pmatrix} \exp [i\kappa_\nu(n)x + ik_y y]$$

$$\mathbf{F}_{K'}(r) = \frac{1}{\sqrt{2}} \begin{pmatrix} b_{-\nu}(n, k_y)^* \\ \pm 1 \end{pmatrix} \exp [i\kappa_{-\nu}(n)x + ik_y y]$$

with

$$b_\nu(n, k_y) = \frac{\kappa_\nu(n) - ik_y}{\sqrt{\kappa_\nu(n)^2 + k_y^2}}.$$

Energy levels

$$\varepsilon_\nu^\pm(n) = \pm \gamma \sqrt{\kappa_\nu(n)^2 + k_y^2}$$

Discretized wave number in circumference direction

$$k_x = \kappa_\nu(n) = \frac{2\pi}{L}(n - \nu/3)$$

Ajiki and Ando, J. Phys. Soc. Jpn., 62, 1255 (1993)

$$n_a + n_b = 3N + \nu$$

$\nu = 0$ **metallic CN**

Linear dispersion

$$\varepsilon_0^\pm(0) = \pm \gamma |k_y|$$

$\nu = \pm 1$ **semiconducting CN**

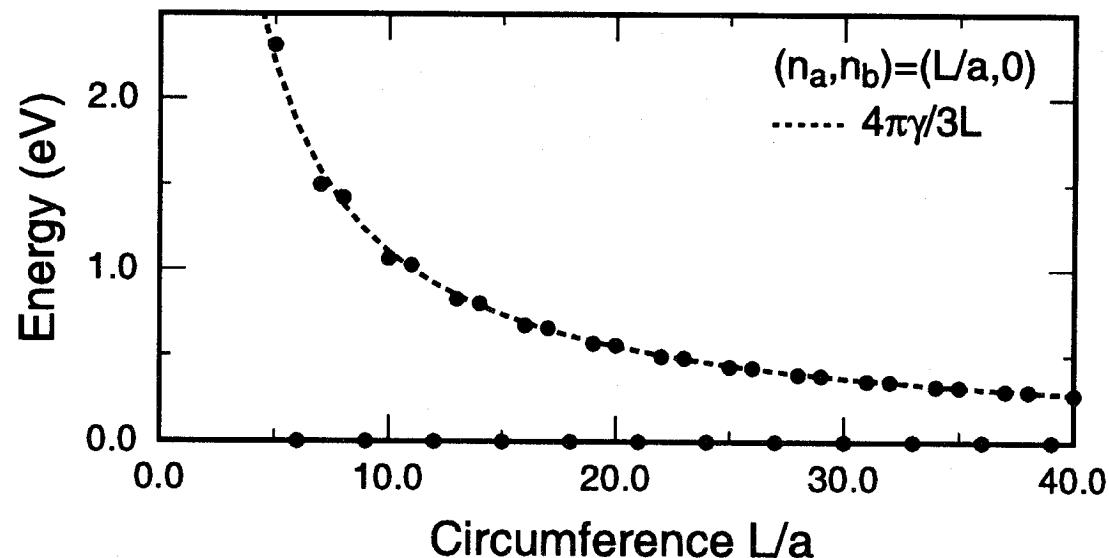
Band gap

$$E_g = 2\gamma |\kappa_{\pm 1}(0)| = \frac{4\pi\gamma}{3L}$$

Band Gap

$$E_g = \frac{4\pi\gamma}{3L}$$

Band Gap of Zigzag Nanotubes



M. S. Dresselhaus, G. Dresselhaus and R. Saito, Sol. State Com., **84**, 201 (1992).

H. Ajiki and T. Ando, J. Phys. Soc. Jpn., **62**, 1255 (1993).

Effective–Potential

T. Ando and T. Nakanishi, J. Phys. Soc. Jpn. **67**, 1704 (1998)

Effective–Mass Equation

$$\begin{aligned}
 & (\mathcal{H}_0 + V)\mathcal{F} = \varepsilon\mathcal{F} \\
 \mathcal{H}_0 = & \begin{pmatrix} 0 & \gamma(\hat{k}_x - i\hat{k}_y) & 0 & 0 \\ \gamma(\hat{k}_x + i\hat{k}_y) & 0 & 0 & 0 \\ 0 & 0 & 0 & \gamma(\hat{k}_x + i\hat{k}_y) \\ 0 & 0 & \gamma(\hat{k}_x - i\hat{k}_y) & 0 \end{pmatrix}, \quad \mathcal{F} = \begin{pmatrix} F_A^K(\mathbf{r}) \\ F_B^K(\mathbf{r}) \\ F_A^{K'}(\mathbf{r}) \\ F_B^{K'}(\mathbf{r}) \end{pmatrix} \\
 V = & \begin{pmatrix} u_A(\mathbf{r}) & 0 & e^{i\eta}u'_A(\mathbf{r}) & 0 \\ 0 & u_B(\mathbf{r}) & 0 & -\omega^{-1}e^{-i\eta}u'_B(\mathbf{r}) \\ e^{-i\eta}u'_A(\mathbf{r})^* & 0 & u_A(\mathbf{r}) & 0 \\ 0 & -\omega e^{i\eta}u'_B(\mathbf{r})^* & 0 & u_B(\mathbf{r}) \end{pmatrix}
 \end{aligned}$$

$$\begin{aligned}
 u_A &= \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_A} \tilde{u}_A(\mathbf{R}_A), \\
 u_B &= \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_B} \tilde{u}_B(\mathbf{R}_B), \\
 u'_A &= \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_A} e^{i(\mathbf{K}' - \mathbf{K}) \cdot \mathbf{R}_A} \tilde{u}_A(\mathbf{R}_A), \\
 u'_B &= \frac{\sqrt{3}a^2}{2} \sum_{\mathbf{R}_B} e^{i(\mathbf{K}' - \mathbf{K}) \cdot \mathbf{R}_B} \tilde{u}_B(\mathbf{R}_B),
 \end{aligned}$$

$\sqrt{3}a^2/2$: Area of a Unit Cell

Slowly-varying Potential

Potential Range $d \ll$ Circumference $L = |\mathbf{L}|$

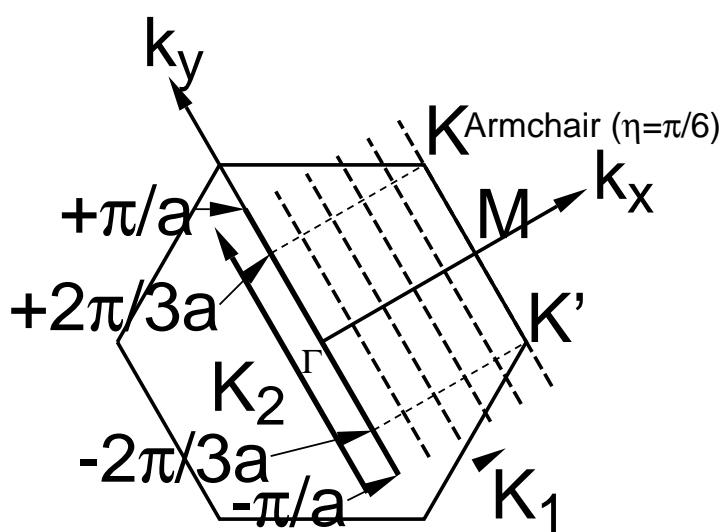
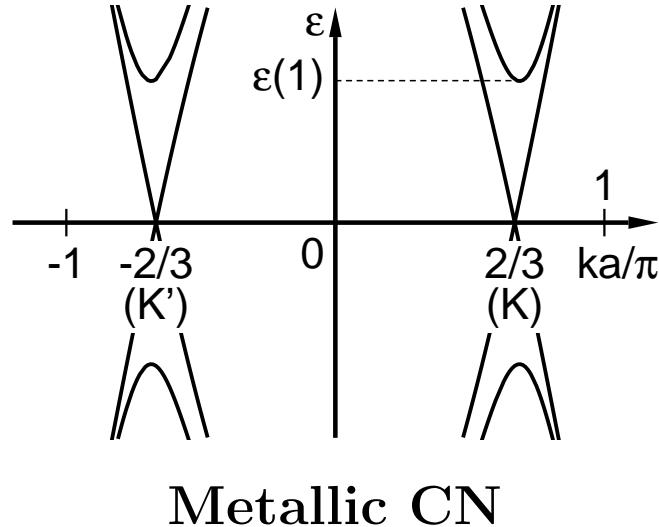
$$\begin{aligned}
 u_A(\mathbf{r}) &= u_A \delta(\mathbf{r} - \mathbf{r}_0), & u_B(\mathbf{r}) &= u_B \delta(\mathbf{r} - \mathbf{r}_0), \\
 u'_A(\mathbf{r}) &= u'_A \delta(\mathbf{r} - \mathbf{r}_0), & u'_B(\mathbf{r}) &= u'_B \delta(\mathbf{r} - \mathbf{r}_0).
 \end{aligned}$$

Potential Range $d \gg a$

$$\begin{aligned}
 u_A(\mathbf{r}) &= u_B(\mathbf{r}) \\
 u'_A(\mathbf{r}) &= u'_B(\mathbf{r}) = 0
 \end{aligned}$$

\mathbf{r}_0 : Impurity Position

Right- and left-going channels



$(n_a, n_b) = (2, 1)m$
armchair CN

○Solutions for $V = 0, |\varepsilon| < \varepsilon(1) = \frac{2\pi\gamma}{L}$

$$\mathbf{F}^{K\pm} = \begin{pmatrix} F_A^K(\mathbf{r}) \\ F_B^K(\mathbf{r}) \end{pmatrix} = \frac{1}{\sqrt{2AL}} \begin{pmatrix} \mp i \\ 1 \end{pmatrix} \exp(iky),$$

$$\mathbf{F}^{K'\pm} = \begin{pmatrix} F_A^{K'}(\mathbf{r}) \\ F_B^{K'}(\mathbf{r}) \end{pmatrix} = \frac{1}{\sqrt{2AL}} \begin{pmatrix} \pm i \\ 1 \end{pmatrix} \exp(iky).$$

A: Length of Nanotube

Energy: $\varepsilon(k) = \pm \gamma k$

Group Velocity: $v = \pm \gamma/\hbar$

$$\pm \left\{ \begin{array}{l} \text{Right-going } \mathbf{F}^{K+}, \mathbf{F}^{K'+} \\ \text{Left-going } \mathbf{F}^{K-}, \mathbf{F}^{K'-} \end{array} \right.$$

Lowest Born Approximation

○ Inter-valley Scattering

$$\begin{aligned}
 V_{K\pm K'+} &= \frac{1}{2AL} \int d\mathbf{r} \begin{pmatrix} \pm i & 1 \end{pmatrix} \begin{pmatrix} e^{i\eta} u'_A(\mathbf{r}) & 0 \\ 0 & -\omega^{-1} e^{-i\eta} u'_B(\mathbf{r}) \end{pmatrix} \begin{pmatrix} i \\ 1 \end{pmatrix} \\
 &= \frac{1}{2AL} \int d\mathbf{r} \{ \mp e^{i\eta} u'_A(\mathbf{r}) - \omega^{-1} e^{-i\eta} u'_B(\mathbf{r}) \} \\
 &= \frac{1}{2AL} (\mp u'_A e^{i\eta} - \omega^{-1} e^{-i\eta} u'_B) = V_{K'\pm K+}^*
 \end{aligned}$$

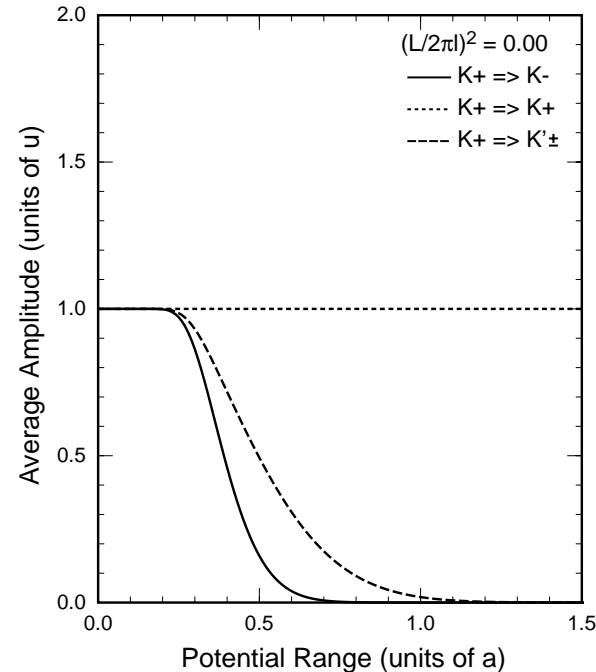
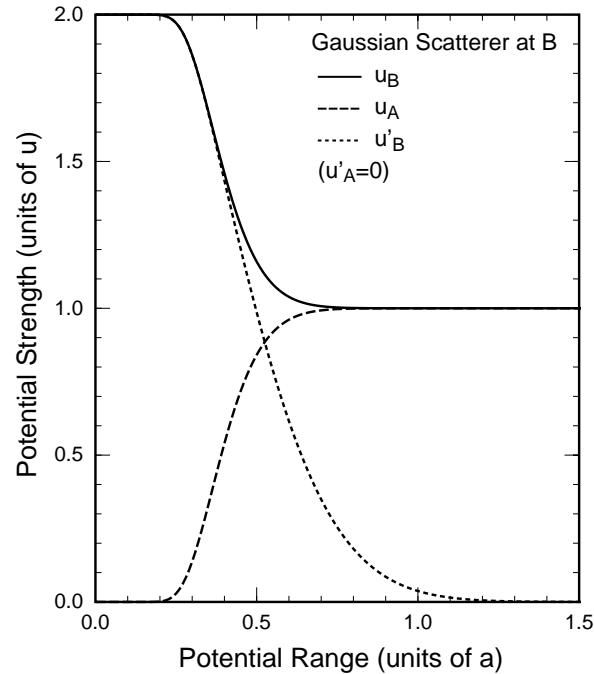
○ Intra-valley Scattering

$$\begin{aligned}
 V_{K\pm K+} &= \frac{1}{2AL} \int d\mathbf{r} \begin{pmatrix} \pm i & 1 \end{pmatrix} \begin{pmatrix} u_A(\mathbf{r}) & 0 \\ 0 & u_B(\mathbf{r}) \end{pmatrix} \begin{pmatrix} -i \\ 1 \end{pmatrix} \\
 &= \frac{1}{2AL} \int d\mathbf{r} \{ \pm u_A(\mathbf{r}) + u_B(\mathbf{r}) \} \\
 &= \frac{1}{2AL} (\pm u_A + u_B) = V_{K'\pm K'+}
 \end{aligned}$$

Absence of back-scattering for slowly varying potential

$$V_{K-K'+} = V_{K'-K+}^* = 0, \quad V_{K-K+} = V_{K'-K'+} \propto u_B - u_A = 0$$

Gaussian Potential



$$V(\mathbf{r}) = \frac{f(d/a)u}{\pi d^2} \exp\left(-\frac{\mathbf{r}^2}{d^2}\right)$$

$f(d/a)$: Normalization Factor

$$\sum_{i=A,B} \sum_{\mathbf{R}_i} \frac{\sqrt{3}a^2}{4} V(\mathbf{R}_i - \mathbf{R}_B^0) = u = (u_A + u_B)/2$$

$d \gg a$: Absence of Back Scattering

↓
Huge Conductivity,
Quantized Conductance

Magnetic Field

Solutions for $V = 0, |\varepsilon| < \varepsilon(1)$

Gauge: $\mathbf{A} = (0, \frac{LH}{2\pi} \sin \frac{2\pi x}{L})$

$$\mathbf{F}_{sk}^K = \begin{pmatrix} F_A^K(\mathbf{r}) \\ F_B^K(\mathbf{r}) \end{pmatrix} = \frac{1}{\sqrt{2A}} \begin{pmatrix} -is(k/|k|)F_-(x) \\ F_+(x) \end{pmatrix} \exp(iky),$$

$$\mathbf{F}_{sk}^{K'} = \begin{pmatrix} F_A^{K'}(\mathbf{r}) \\ F_B^{K'}(\mathbf{r}) \end{pmatrix} = \frac{1}{\sqrt{2A}} \begin{pmatrix} +is(k/|k|)F_+(x) \\ F_-(x) \end{pmatrix} \exp(iky).$$

$$F_{\pm}(x) = \frac{1}{\sqrt{LI_0(\alpha)}} \exp \left[\pm \frac{1}{2} \alpha \cos \frac{2\pi x}{L} \right]$$

$\alpha = 2 \left(\frac{L}{2\pi l} \right)^2$: Magnetic Field

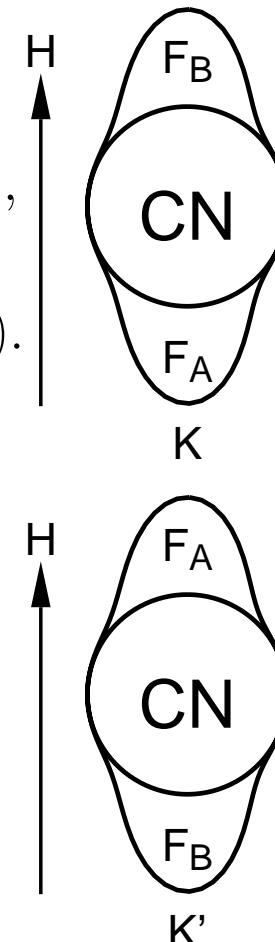
$l = \sqrt{c\hbar/eH}$: Magnetic Length

$I_0(z)$: Modified Bessel function of the first kind

$$I_0(z) = \int_0^\pi \frac{d\theta}{\pi} \exp(z \cos \theta)$$

$s = +1$ conduction band

$s = -1$ valence band



T. Ando and T. Seri, J. Phys. Soc. Jpn. 66, 3558 (1997)

Back scatterings in magnetic field

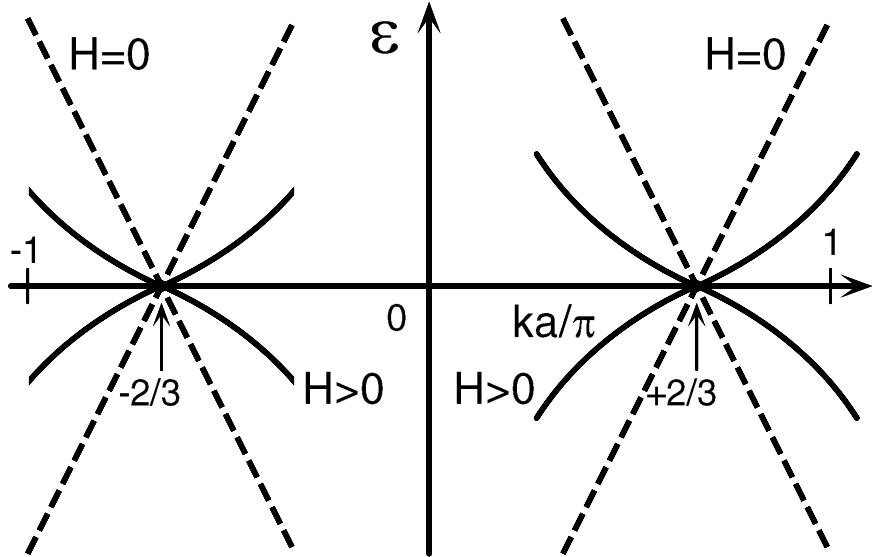
Energy

$$\varepsilon(k) = s\gamma|k|I_0(\alpha)^{-1}$$

$(n_a, n_b) = (2, 1)m$: armchair CN

Dashed lines: $H = 0$

Solid lines: $H \neq 0$



Lowest Born Approximation

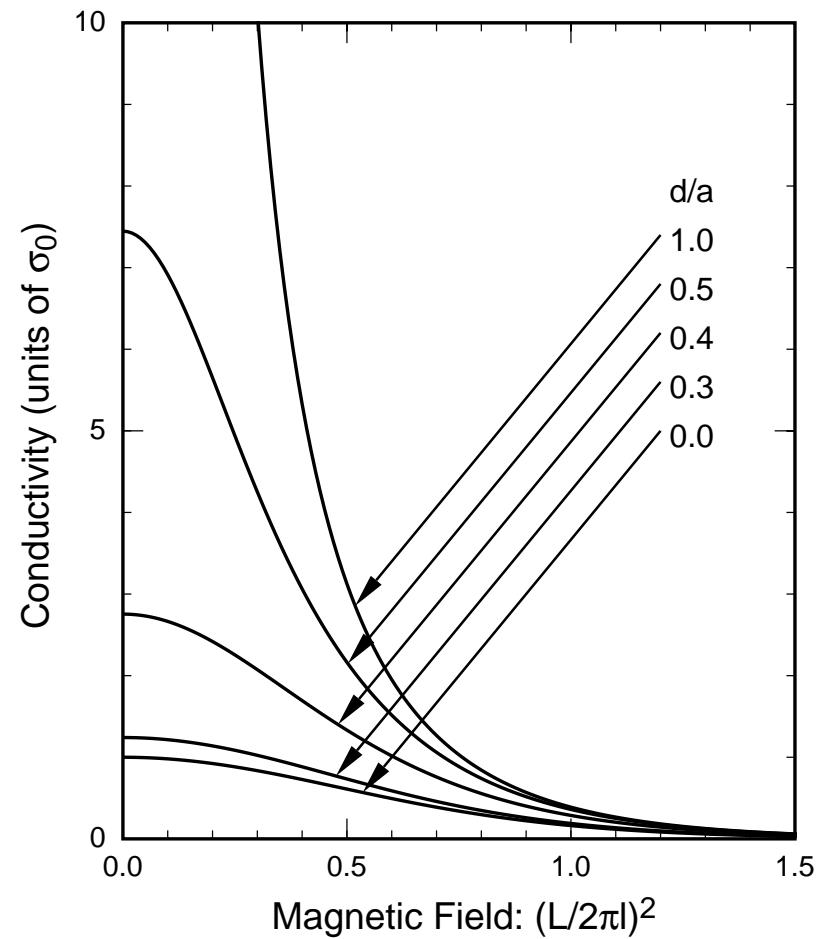
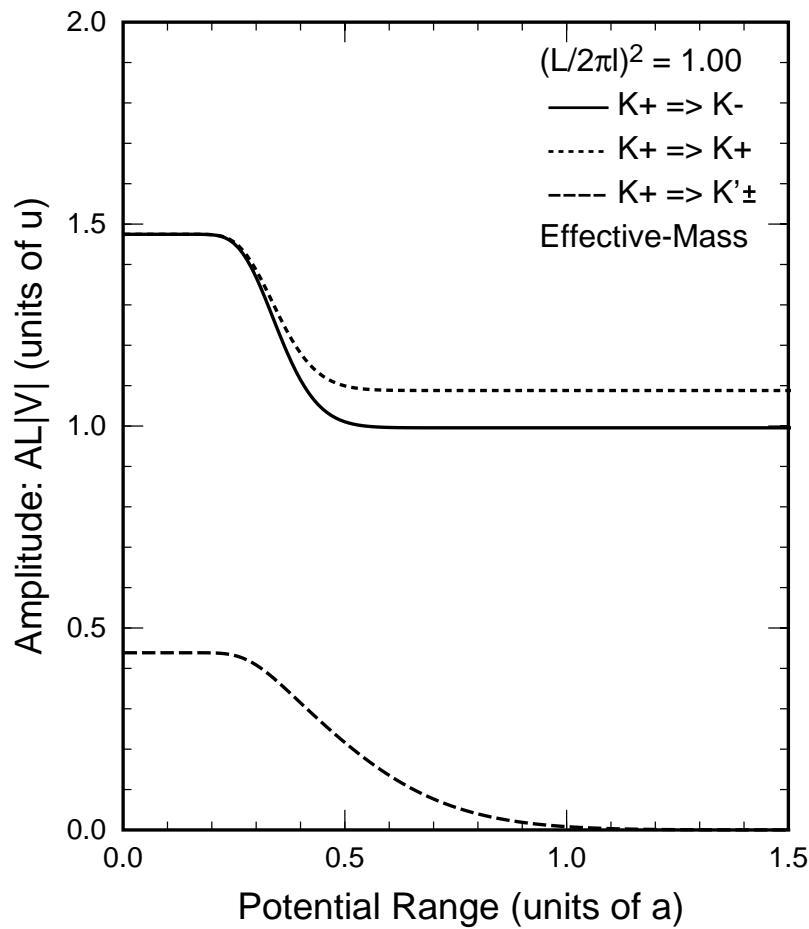
○ Inter-valley Scattering

$$V_{K\pm K'+} = \frac{1}{2A} (\mp u'_A e^{i\eta} - \omega^{-1} e^{-i\eta} u'_B) F_+(x_0) F_-(x_0) = V_{K'\pm K+}^*$$

○ Intra-valley Scattering

$$V_{K\pm K+} = \frac{1}{2A} (\pm u_A F_-(x_0)^2 + u_B F_+(x_0)^2) = V_{K'\pm K'+}$$

Dependence on the Magnetic Field Huge Positive Magnetoresistance



Boltzmann conductivity

$$\sigma_0 = \frac{e^2}{2\pi\hbar} \Lambda, \quad \Lambda = \frac{\tau\gamma}{\hbar}, \quad \frac{\hbar}{\tau} = \frac{4n_i \langle u^2 \rangle}{\gamma L}$$

Absence of Back Scattering($d \gg a$)

$$T = V + V \frac{1}{\varepsilon - \mathcal{H}_0} V + V \frac{1}{\varepsilon - \mathcal{H}_0} V \frac{1}{\varepsilon - \mathcal{H}_0} V + \dots$$

$$\mathcal{H}_0 = \gamma \begin{pmatrix} 0 & \hat{k}_x - i\hat{k}_y \\ \hat{k}_x + i\hat{k}_y & 0 \end{pmatrix}$$

$$\varepsilon_s(-\mathbf{k}) = \varepsilon_s(\mathbf{k})$$

$$\mathbf{F}_{s\mathbf{k}} = \exp[i\phi_s(\mathbf{k})] R^{-1}[\theta(\mathbf{k})] |s\rangle,$$

$$k_x + ik_y = i|\mathbf{k}|e^{i\theta(\mathbf{k})}$$

Spin-rotation operator

$$R(\theta) = \exp\left(i\frac{\theta}{2}\sigma_z\right)$$

$$\begin{aligned} \mathbf{k} &= \begin{pmatrix} \exp(+i\theta/2) & 0 \\ 0 & \exp(-i\theta/2) \end{pmatrix} \\ &\quad \text{where } \theta(k) = \tan^{-1}(k_y/k_x) \end{aligned}$$

— Long range Potential —

$$V = \begin{pmatrix} V(\mathbf{r}) & 0 \\ 0 & V(\mathbf{r}) \end{pmatrix}$$

$$\mathbf{F}_{s\mathbf{k}}(\mathbf{r}) = \frac{1}{\sqrt{LA}} \exp(i\mathbf{k} \cdot \mathbf{r}) \mathbf{F}_{s\mathbf{k}},$$

$$\varepsilon_s(\mathbf{k}) = s\gamma|\mathbf{k}|,$$

$s = +1$ conduction band

$s = -1$ valence band

Absence of Back Scattering($d \gg a$)

T. Ando and T. Nakanishi, J. Phys. Soc. Jpn. **67**, 1704 (1998)

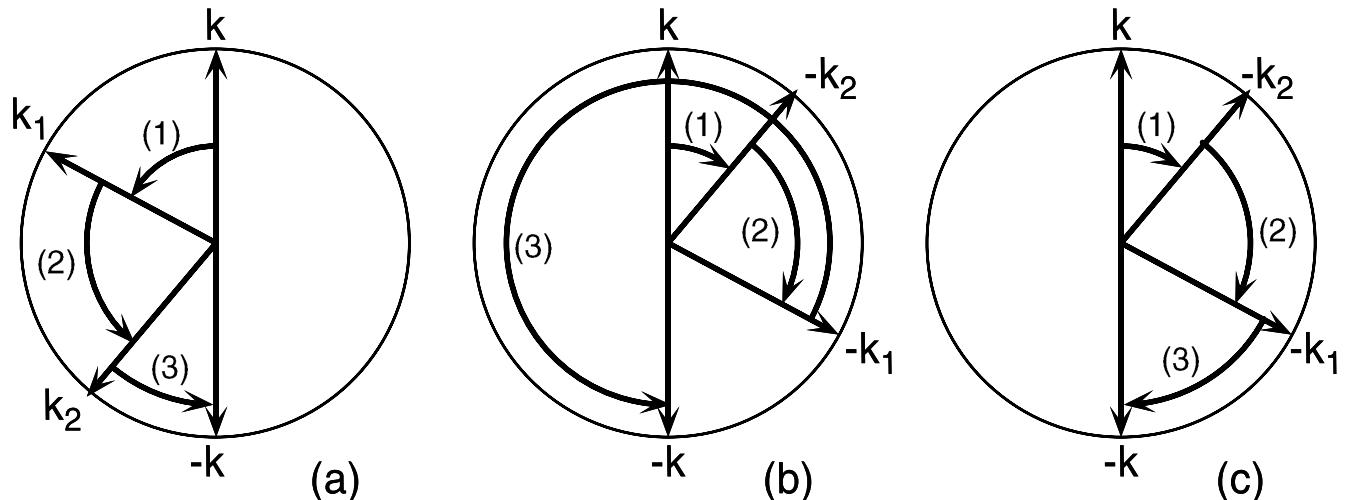
$(p+1)\text{th}$ order term

$$\begin{aligned}
 (s, -\mathbf{k}|T^{(p+1)}|s, +\mathbf{k}) &= \frac{1}{LA} \sum_{s_1 \mathbf{k}_1} \frac{1}{LA} \sum_{s_2 \mathbf{k}_2} \cdots \frac{1}{LA} \sum_{s_p \mathbf{k}_p} \\
 &\times \frac{V(-\mathbf{k} - \mathbf{k}_p) \cdots V(\mathbf{k}_2 - \mathbf{k}_1) V(\mathbf{k}_1 - \mathbf{k})}{[\varepsilon - \varepsilon_{s_p}(\mathbf{k}_p)] \cdots [\varepsilon - \varepsilon_{s_2}(\mathbf{k}_2)][\varepsilon - \varepsilon_{s_1}(\mathbf{k}_1)]} \\
 &\times e^{-i\phi_s(-\mathbf{k})} (s|R[\theta(-\mathbf{k})]R^{-1}[\theta(\mathbf{k}_p)]|s_p) \\
 &\times \cdots \times (s_2|R[\theta(\mathbf{k}_2)]R^{-1}[\theta(\mathbf{k}_1)]|s_1) \\
 &\times (s_1|R[\theta(\mathbf{k}_1)]R^{-1}[\theta(\mathbf{k})]|s)e^{i\phi_s(\mathbf{k})}
 \end{aligned}$$

time-reversal terms
cancel out

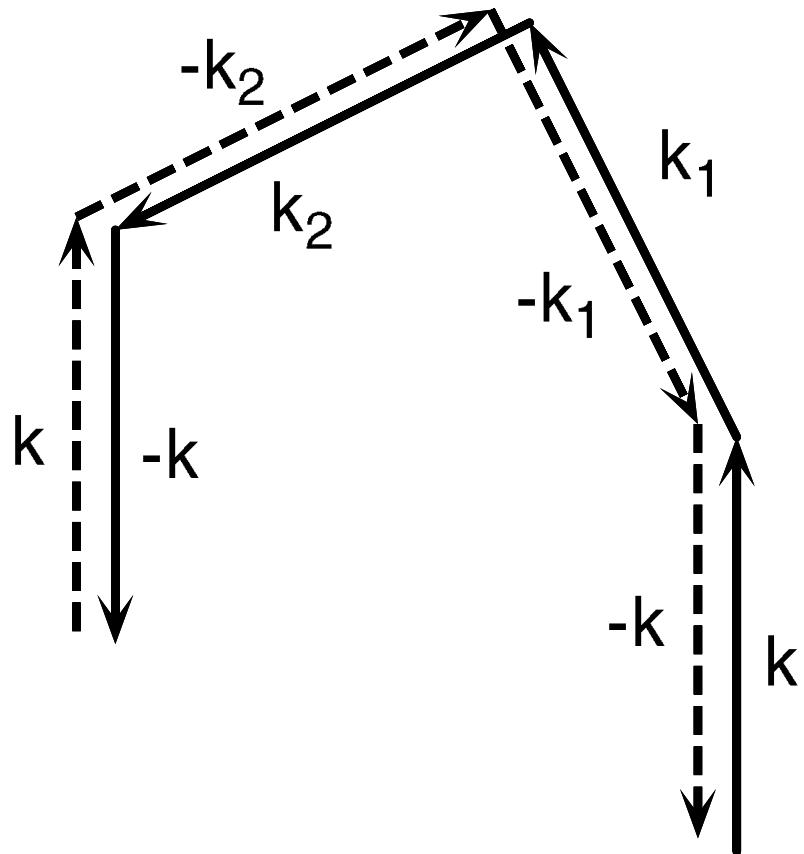
$$\begin{aligned}
 (s_1, k_1) &\rightarrow (s_p, -k_p), \\
 (s_2, k_2) &\rightarrow (s_{p-1}, -k_{p-1}), \dots \\
 R[\theta] &= -R[\theta + 2\pi]
 \end{aligned}$$

$$\varepsilon_s(-\mathbf{k}) = \varepsilon_s(\mathbf{k})$$



Berry's Phase and Absence of Back Scattering

T. Ando, T. Nakanishi, and R. Saito, J. Phys. Soc. Jpn. **67**, 2857 (1998)



$$\psi_s(\mathbf{k}) = \frac{1}{\sqrt{2}} \begin{pmatrix} -is \\ \exp[i\theta(\mathbf{k})] \end{pmatrix}$$

$$\psi_s(\mathbf{k}) \longrightarrow \psi_s(\mathbf{k}) \exp(-i\varphi)$$

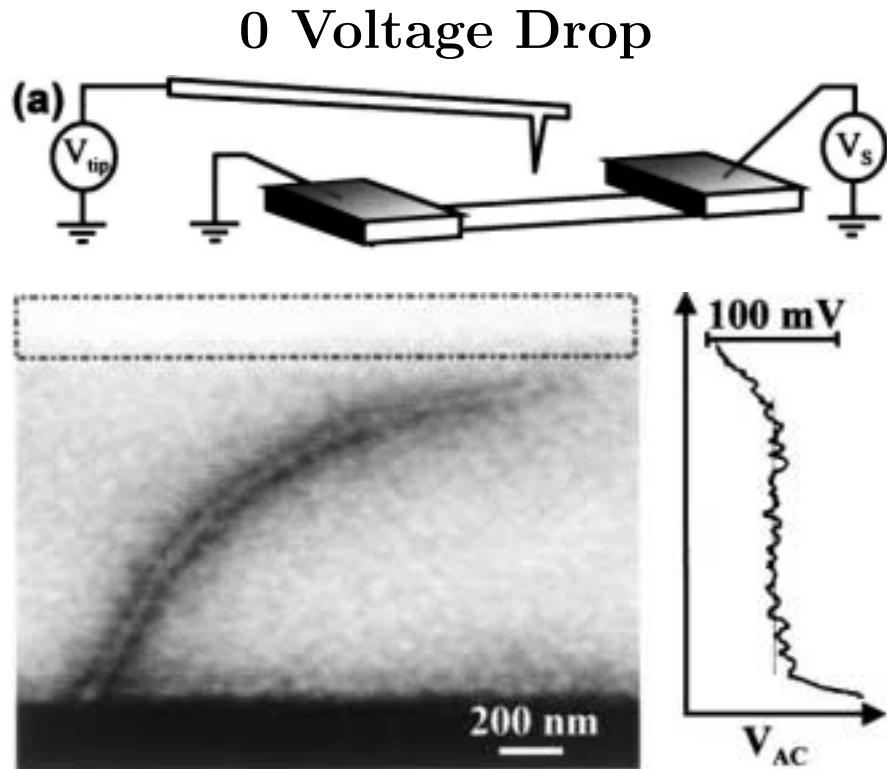
— Berry's Phase —

$$\varphi = -i \int_0^T dt \left\langle \psi_s[\mathbf{k}(t)] \left| \frac{d}{dt} \psi_s[\mathbf{k}(t)] \right. \right\rangle = \pi$$

$$R[\theta - 2\pi] = -R[\theta]$$

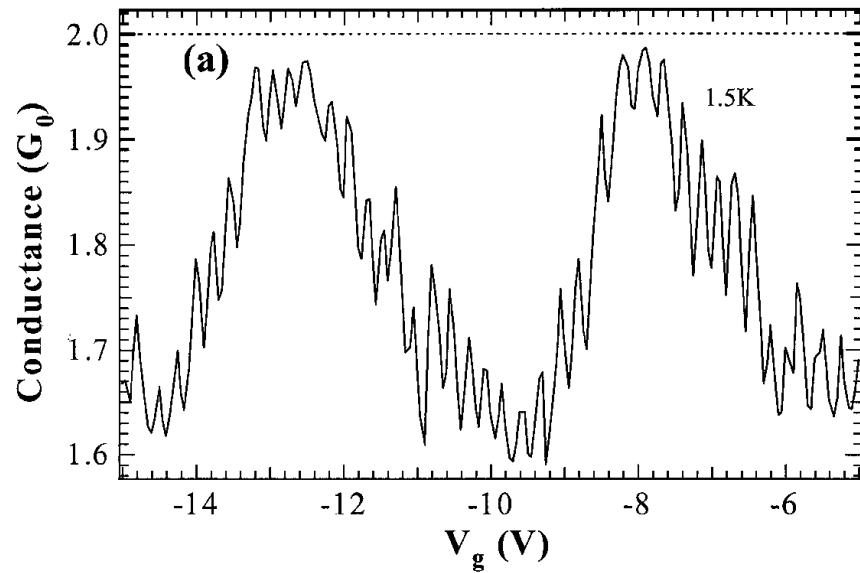
$$R[-\pi] = -R[\pi]$$

Experiments



Bachtold *et al.* (Basel) PRL **84** (2000) 6082

Good Contact $2G_0 = 4e^2/h$
Almost perfect transmission

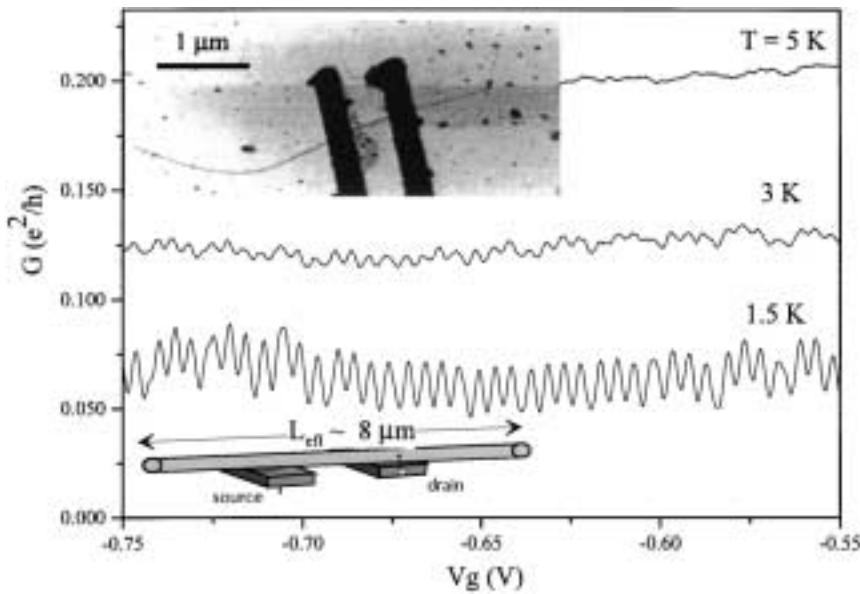


J. Kong *et al.* (Stanford) PRL **87** (2001) 106801

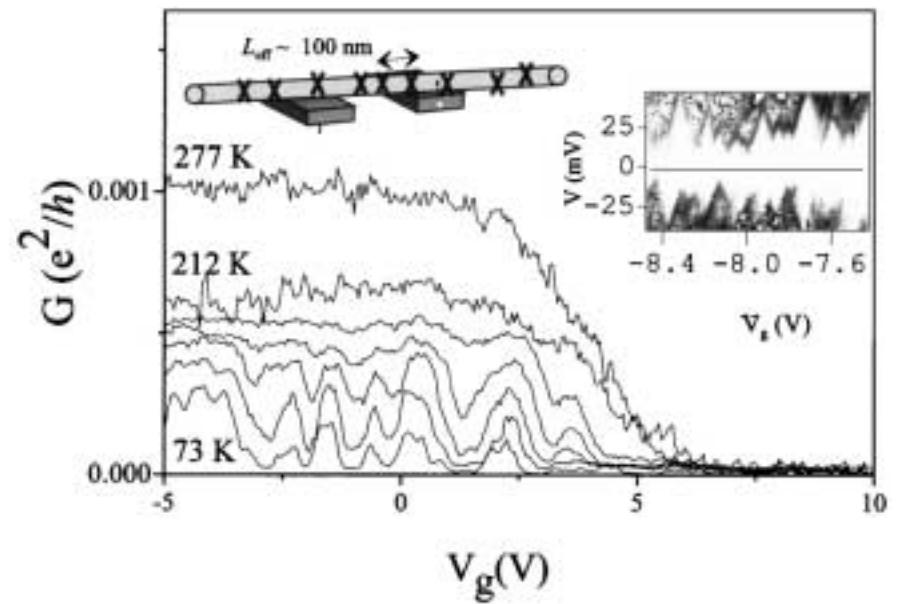
Experiments

Coulomb oscillations

Metallic CN
 $(L_{eff} \sim 8\mu\text{m})$



Semiconducting CN
 $(L_{eff} \sim 100\text{nm})$



Single dot

P. L. McEuen *et al.* (Berkeley) PRL **83** (1999) 5098

Dots in series

Impurity Potential in Carbon Nanotubes

1. Metallic CN and Semiconducting CN

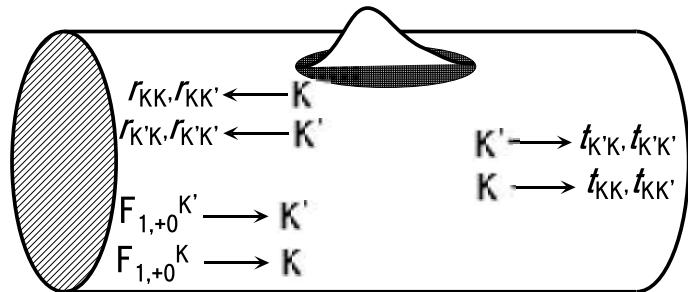
Linear dispersion

2. Absence of Back Scattering

(Long-Range Potential)

Ballistic transport, Huge Conductivity

Berry's Phase, Huge Positive Magnetoresistance



What is impurity?

Long-Range: Nano Particle, Metallic Particle, etc.,

Short-Range: Lattice Defects

Tight-Binding Model

T. Nakanishi, and T. Ando, J. Phys. Soc. Jpn. **68**, 561 (1999)

$$\text{○Landauer's Formular } G = \frac{2e^2}{h} \sum_{m,n} |t_{mn}|^2,$$

t_{mn} : Transmission Coefficients

r_{mn} : Reflection Coefficients

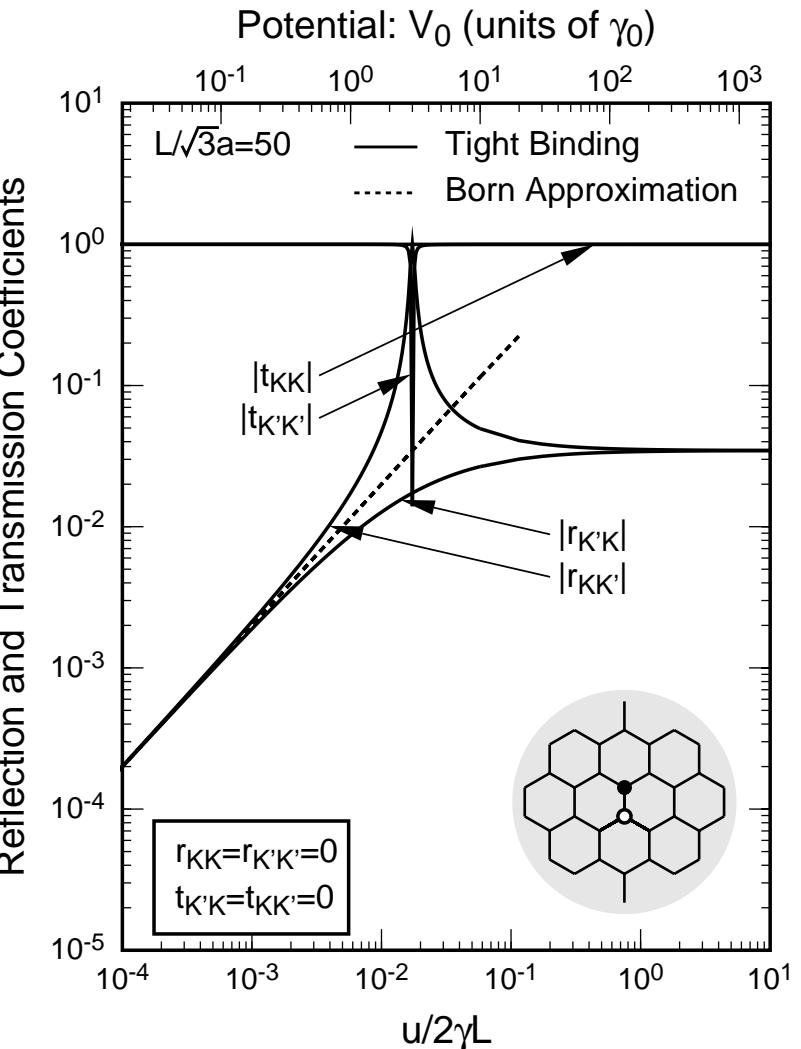
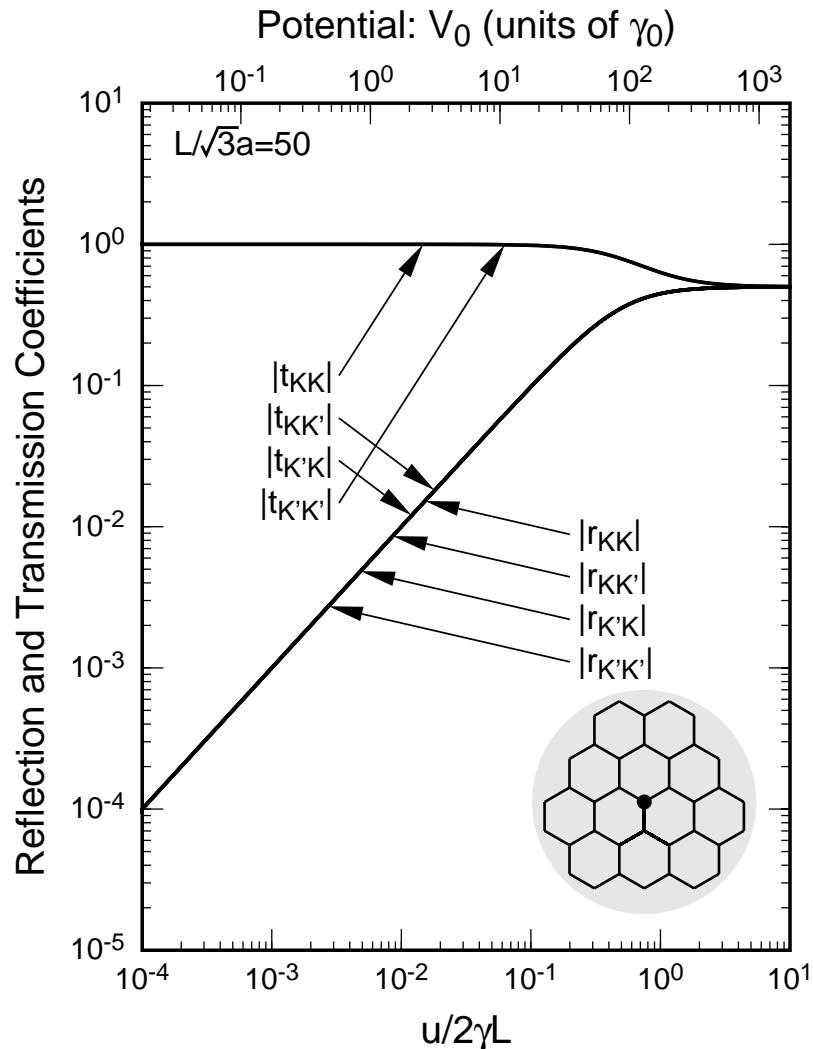
Recursive Green's Function Technique

$\{m, n\} = \{\mathbf{K}, \mathbf{K}\}, \{\mathbf{K}', \mathbf{K}\},$
 $\{\mathbf{K}, \mathbf{K}'\}, \{\mathbf{K}', \mathbf{K}'\}$

T. Ando: PRB**42**, 5626 (1990).

Short Range Potential ($d/a \rightarrow 0$)

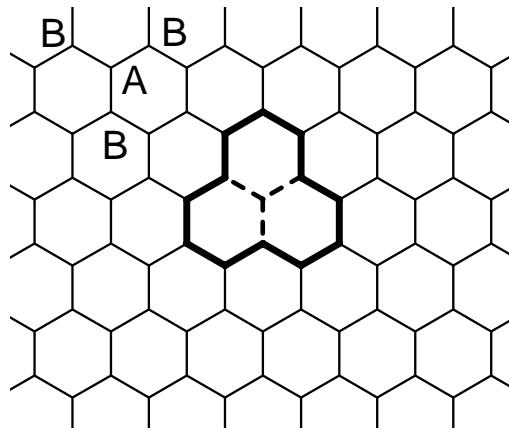
T. Ando, T. Nakanishi, and R. Saito, Microelectronic Engineering, 47 (1999) 421



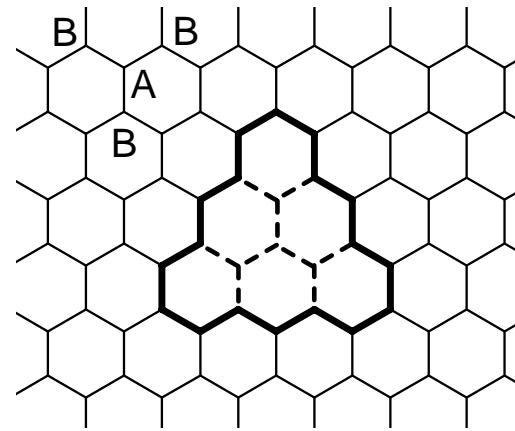
Lattice Vacancy and Conductance Quantization at $\varepsilon = 0$

M. Igami, T. Nakanishi, and T. Ando, J. Phys. Soc. Jpn. **68**, 716 (1999)

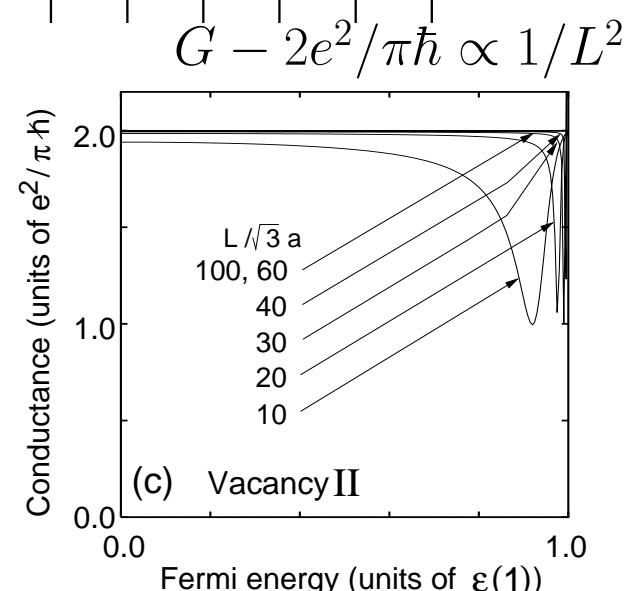
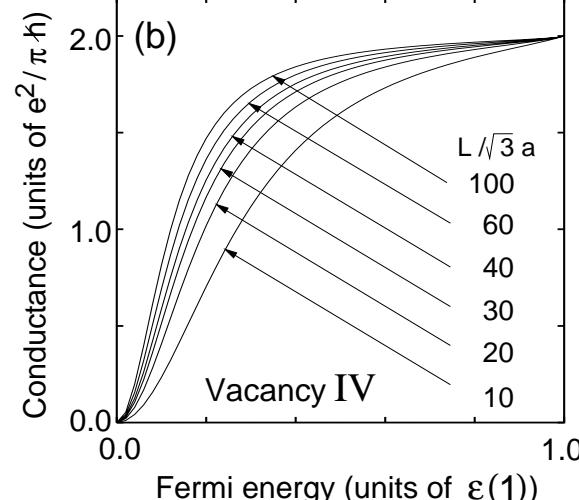
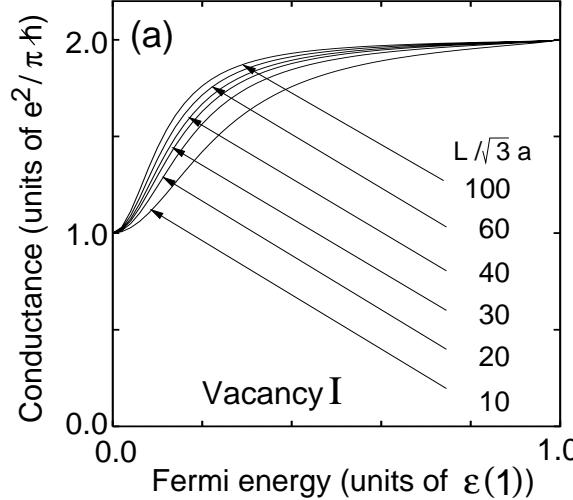
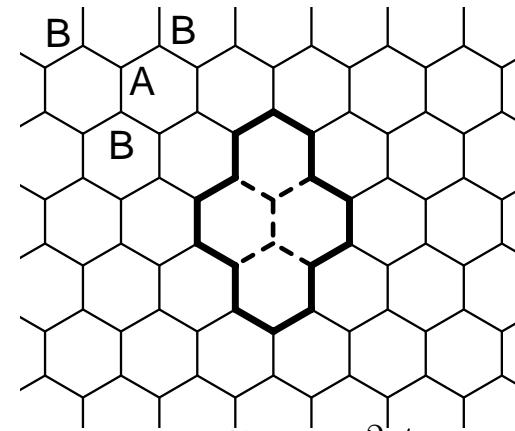
(a) Vacancy I



(b) Vacancy IV

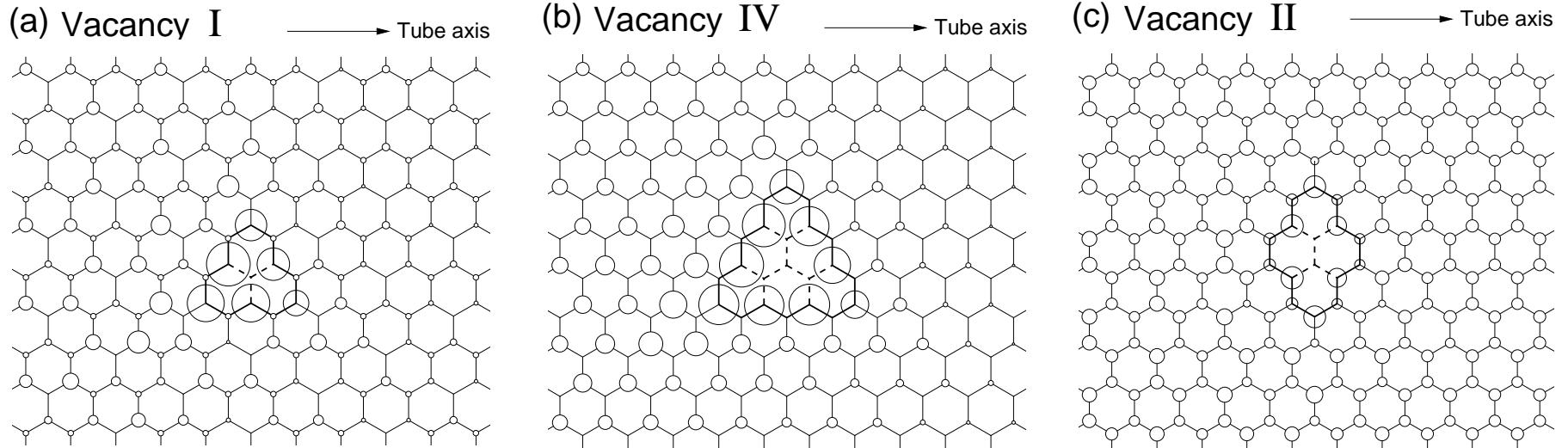


(c) Vacancy II



$$G - 2e^2/\pi\hbar \propto 1/L^2$$

Wave Functions at $\varepsilon = 0$

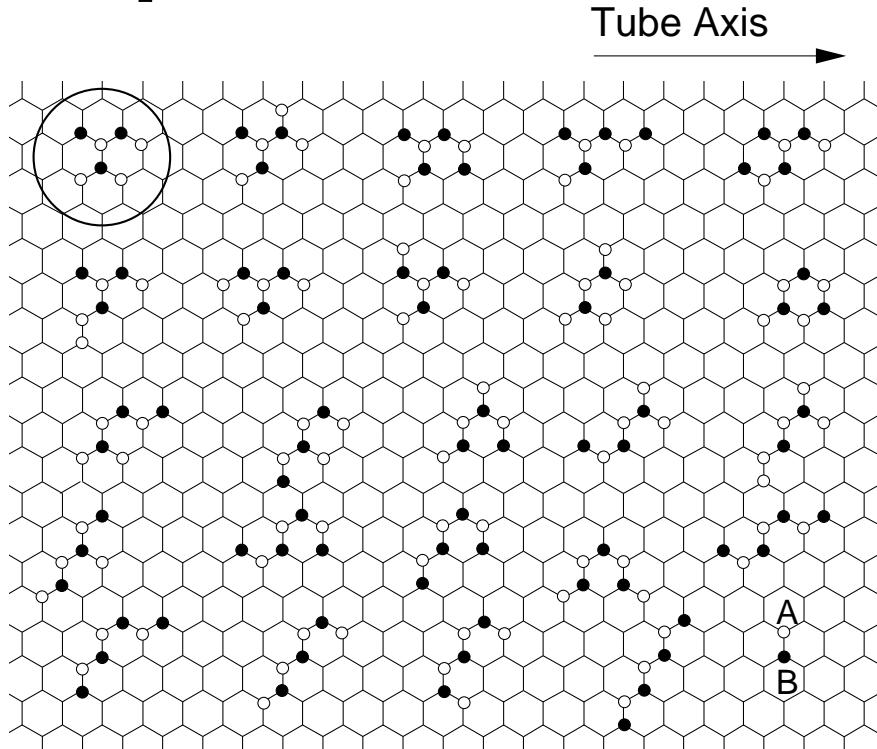


1. Vacancy I: three sublattice Kekulé pattern
Standing Wave (K and K' point)
2. Vacancy IV: Large amplitude at B sites
no component on A sites (left-hand side)
3. Vacancy II: not disturbed by the vacancy

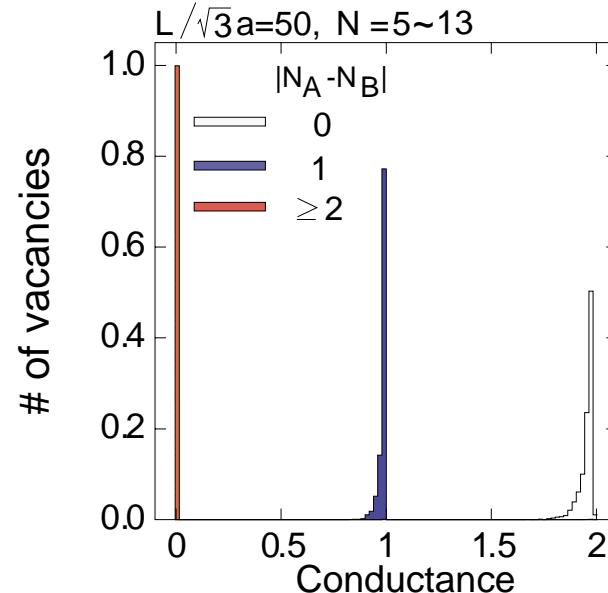
Quantization Rule at $\varepsilon = 0$

M. Igami, T. Nakanishi, and T. Ando, J. Phys. Soc. Jpn. 68 (1999) 3146

Examples for $N = N_A + N_B = 7$



1.6×10^5 different CN's with a vacancy

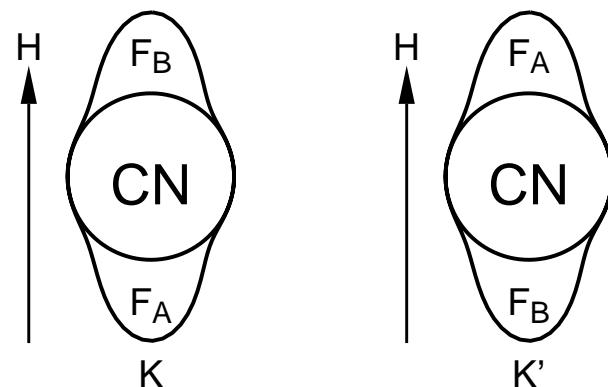
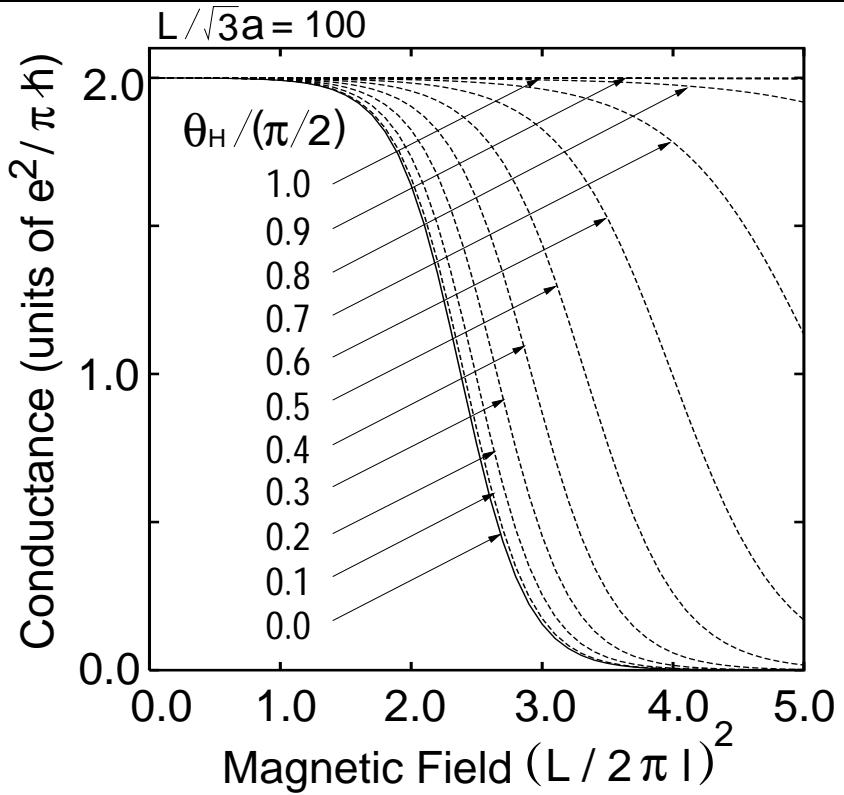
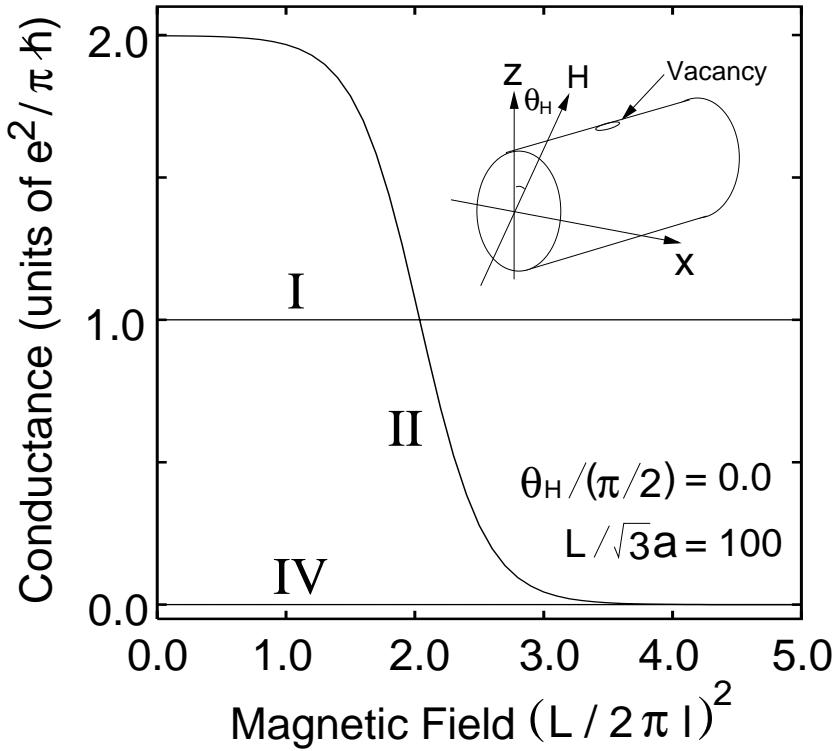


Quantization Rule at $\varepsilon = 0$

N_A, N_B : number of removed A and B sublattice sites

$ N_A - N_B $	1	The Others (≥ 2)	0
Conductance	$e^2/\pi\hbar$	0	$\sim 2e^2/\pi\hbar$

Magnetic Field



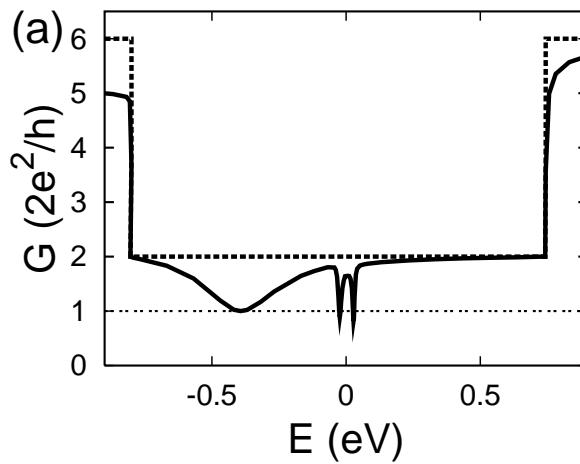
Solid Line: Conductance vs. $H \cos \theta_H$

M. Igami, T. Nakanishi, and T. Ando,
J. Phys. Soc. Jpn. **68**, 716 (1999)

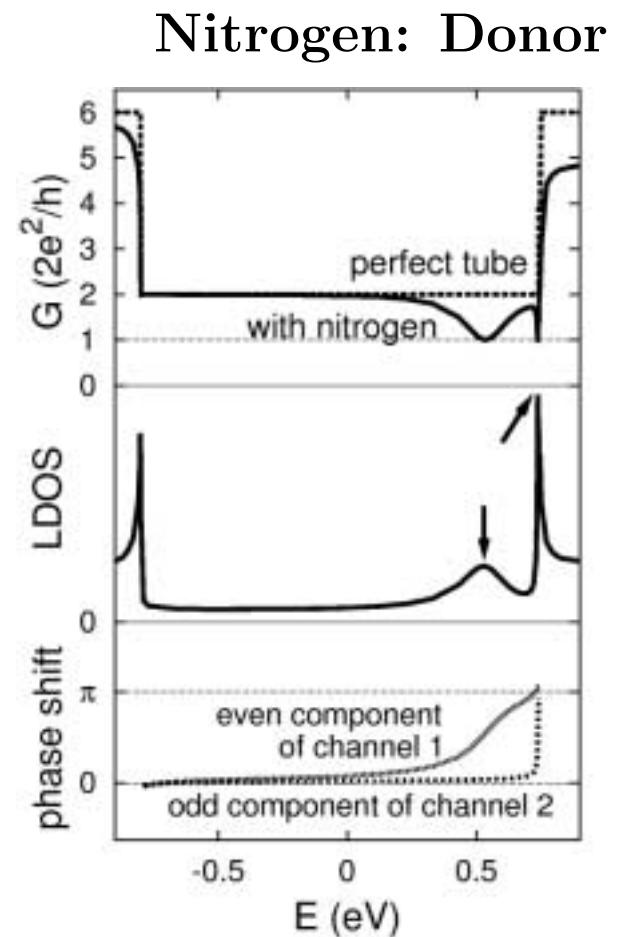
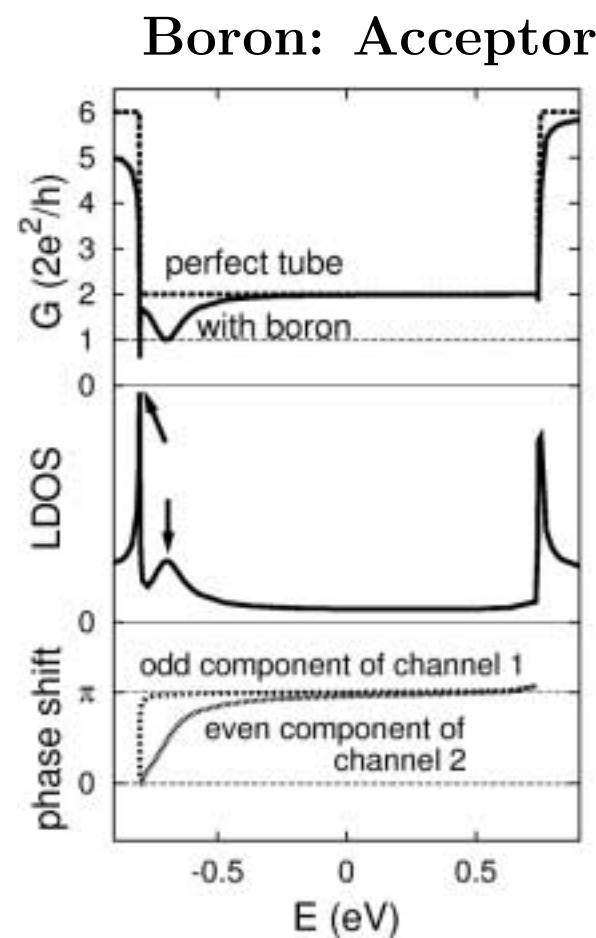
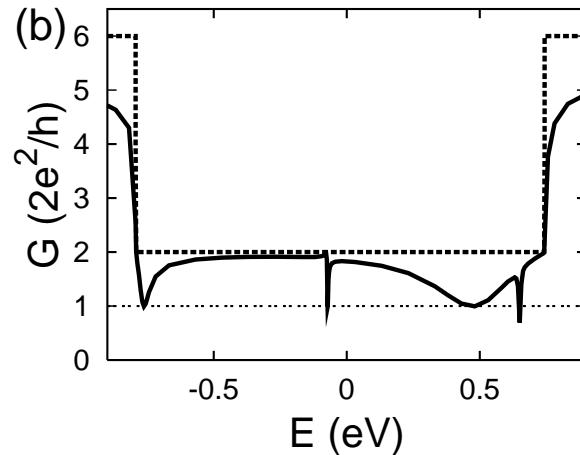
Defects in Carbon Nanotubes

H. J. Choi, et al. PRL 84, 2917 (2000)

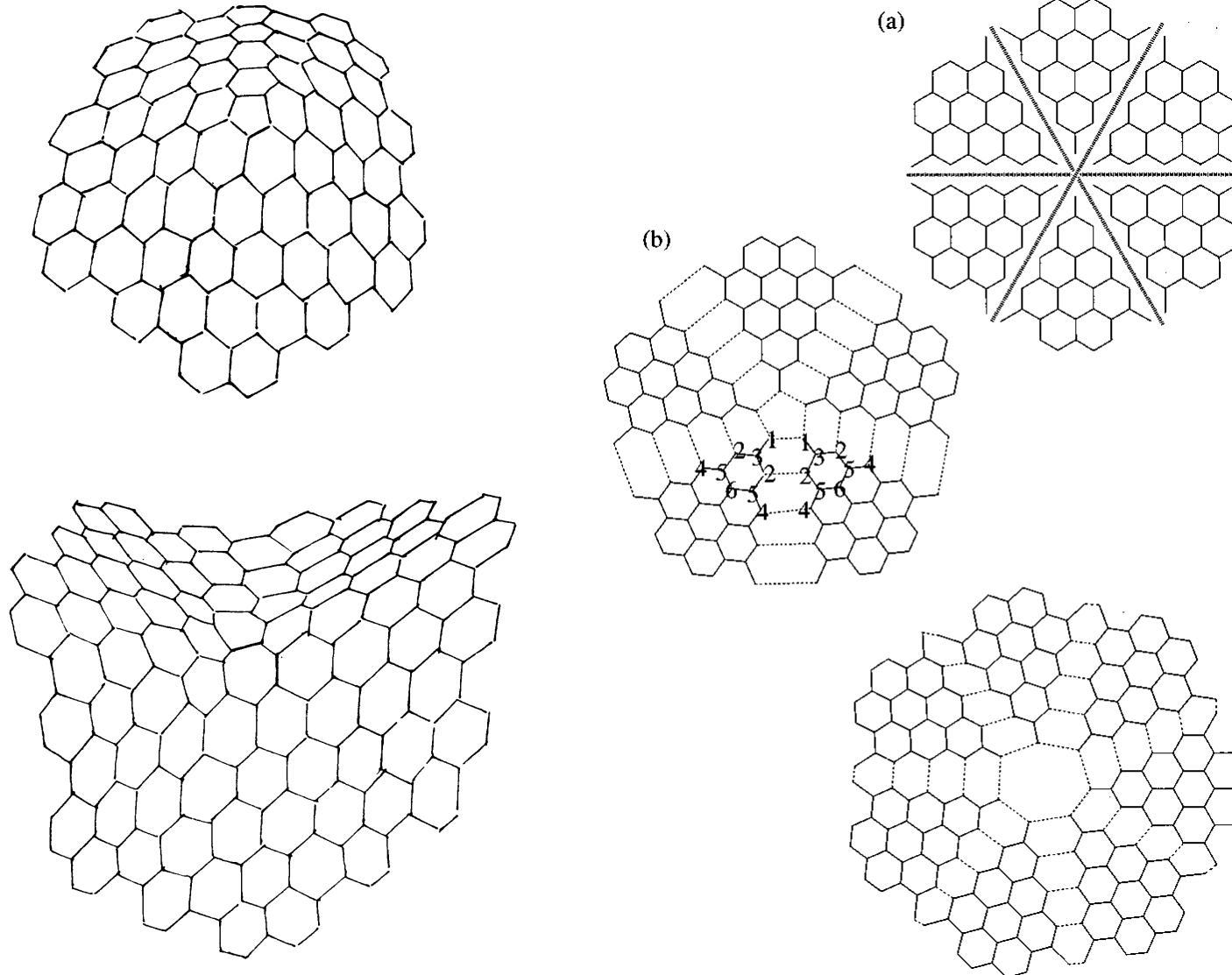
ab initio study on transport in CN with B and N Point vacancy



Double vacancy

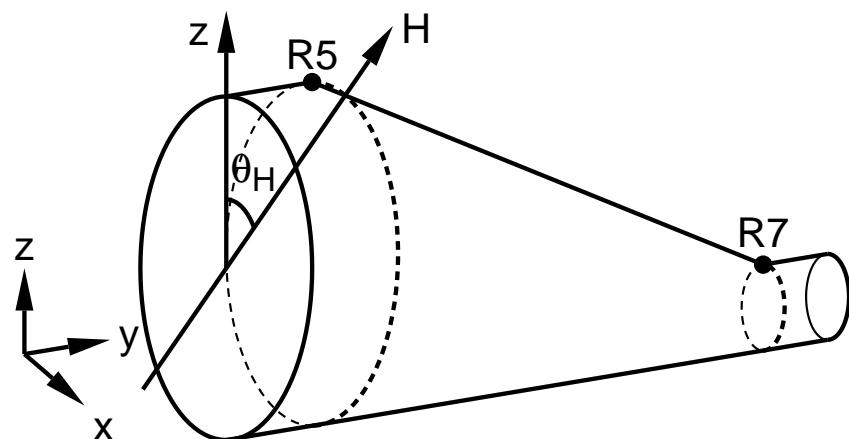
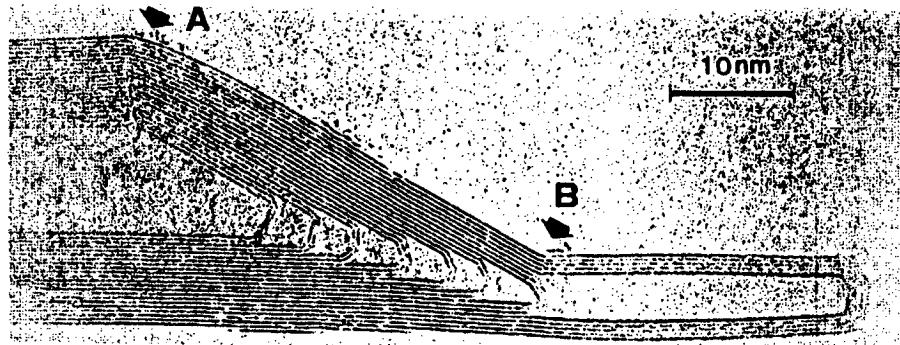


Topological Defects

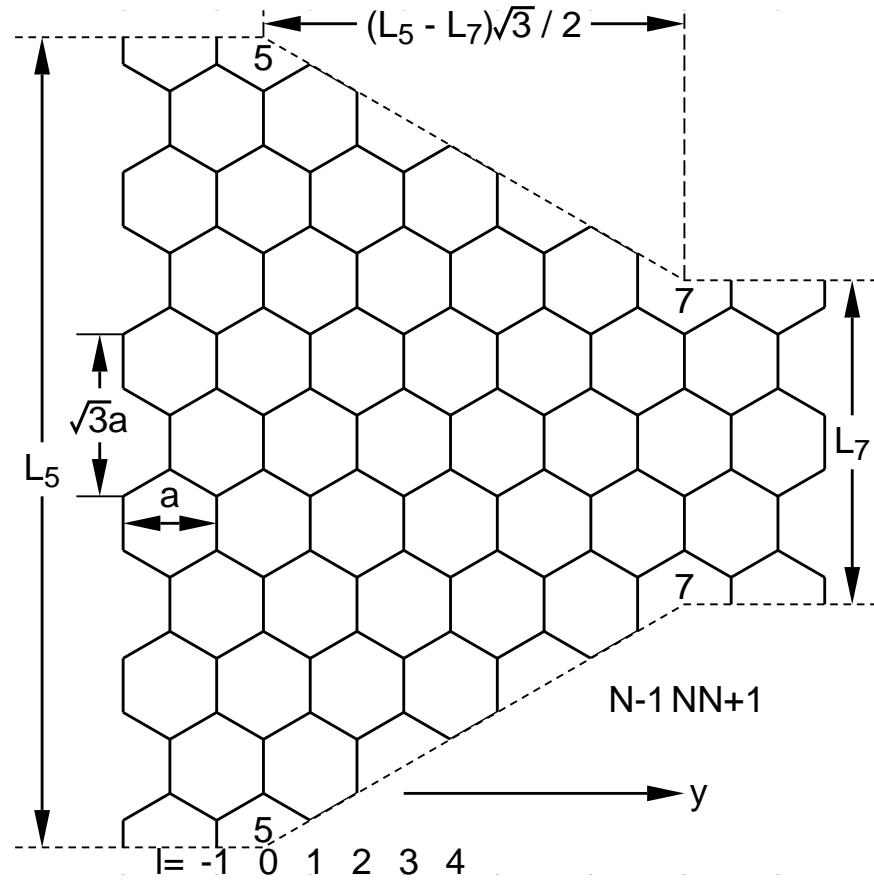


Carbon Nanotube Junction

S. Iijima, T. Ichihashi and Y. Ando, Nature (London), **356**, 776 (1992).



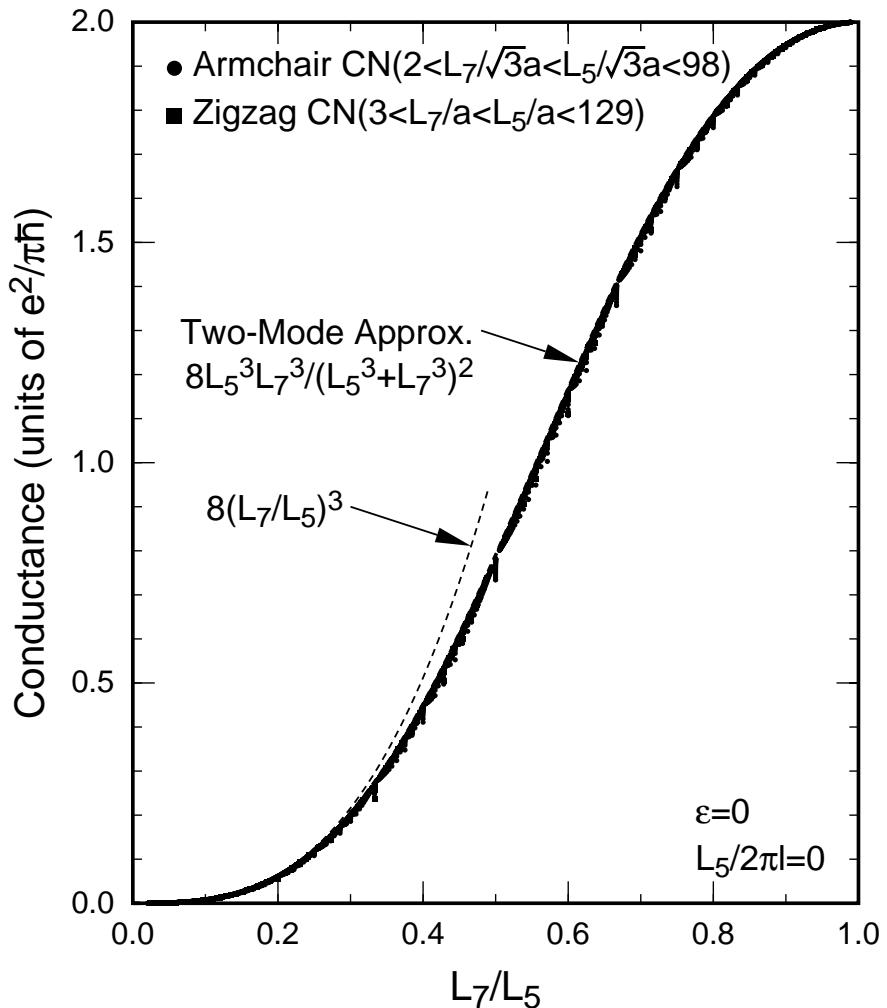
R5 (A): five-membered ring



R7 (B): seven-membered ring

Conductance of CN Junctions ($H = 0$)

R. Tamura and M. Tsukada, PRB55, 4991 (1997).



Conductance exhibits a universal power-law dependence on L_7/L_5

$$G \propto (L_7/L_5)^3 \quad \text{for } L_5 \gg L_7.$$

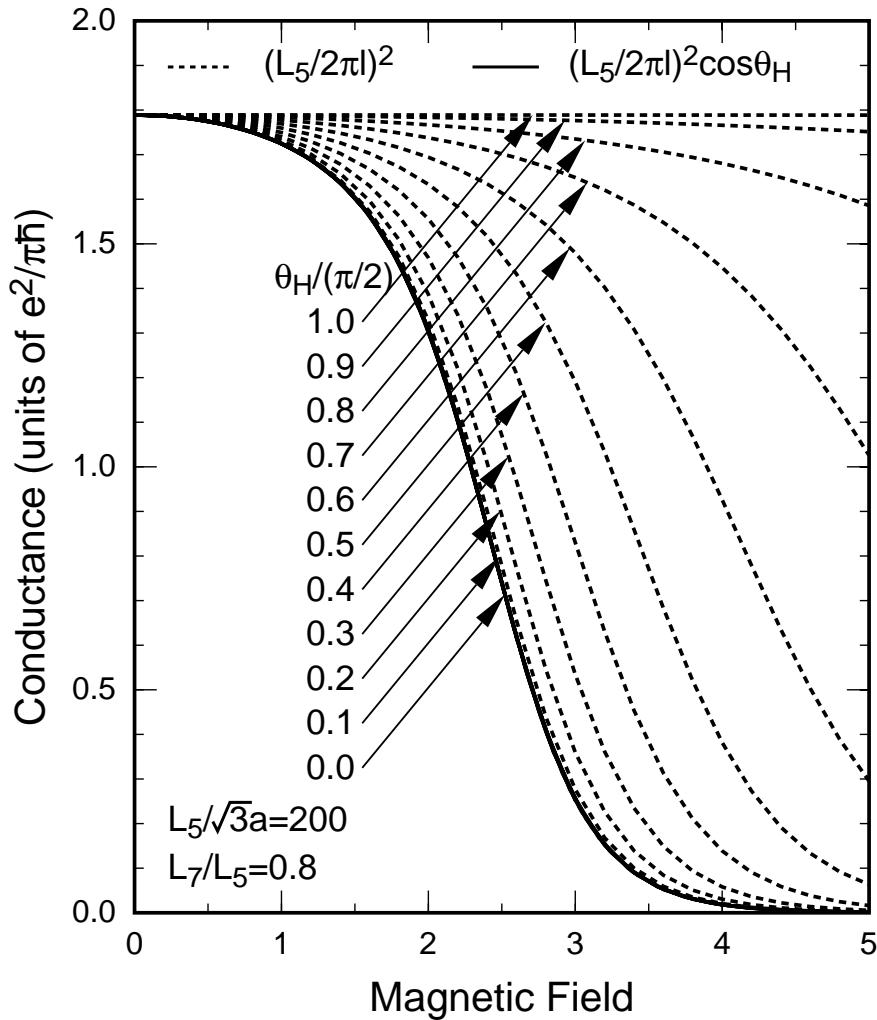
Effective-Mass Theory

Wave function decay linearly

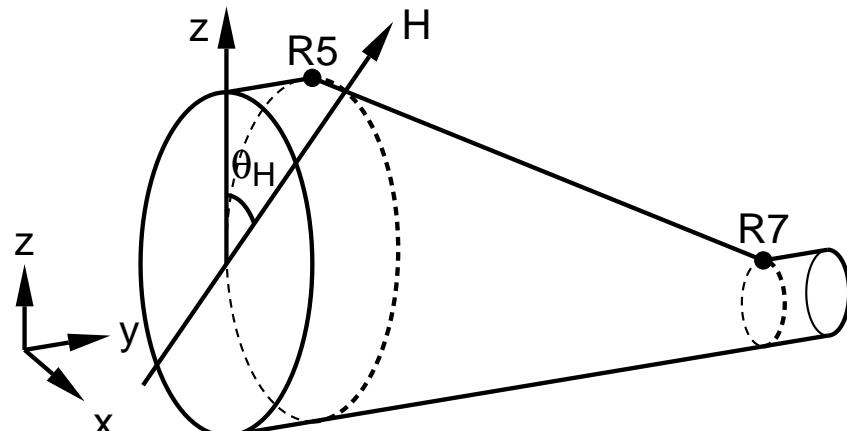
H. Matsumura and T. Ando, J. Phy. Soc. Jpn., 67, 3542 (1998).

CN Junction with Magnetic Field

T. Nakanishi and T. Ando, J. Phys. Soc. Jpn., **66**, 2973 (1997)



Conductance depends only on z component of H



Solid Line: Conductance vs. $H \cos \theta_H$

Conclusion

Interesting Electronic Properties of Carbon nanotubes

1. Long quasi-one dimensional system
2. Metallic CN and Semiconducting CN
3. Linear dispersion
4. Neutrinos on cylinder surface

Collaborators

Tsuneya Ando (ISSP→TIT)
Masatsura Igami (NISTEP)
Riichiro Saito (Tohoku Univ.)

Quantum transport in Carbon Nanotubes

1. Absence of Back Scattering for Long-Range Potential
Ballistic transport, Huge conductivity, Quantized conductance,
Berry's phase,
Huge positive magnetoresistance
2. Lattice Vacancy
Conductance quantization, Donor and accepter
3. Carbon Nanotube Junctions